

Amendments to the Claims

Claims 1, 8 and 11 are currently amended. Claims 2 – 3, 6 – 7, 9 – 10, 12 and 14 – 15 are previously presented. Claims 4 – 5 and 13 are original. Claims 16 – 20 are new. No new matter is added by these amendments. Consideration of all amendments is
5 respectfully requested.

Listing of Claims

Claim 1 (currently amended): A method for determining the integrity of a possibly
10 defected memory under a plurality of operating environments comprising:
setting a plurality of operating environments respectively corresponding to
variations in a condition to be tested;
repeatedly testing the same memory under each of the plurality of operating
environments;
15 recording a result of the testing step for each of the plurality of operating
environments; and
comparing the recorded results for each of the plurality of operating
environments, wherein if the results are the same for each of the plurality
of operating environments then the memory is determined to have
20 integrity.

Claim 2 (previously presented): The method of claim 1, wherein the testing step further
comprises:
performing a built-in self test (BIST) on the memory under each of the plurality
25 of operating environments.

Claim 3 (previously presented): The method of claim 2 further comprising:
marking a status record memory according to the BIST, wherein the status record

memory corresponds to the memory; and
recording the content of the status record memory for each of the plurality of
operating environments.

5 Claim 4 (original): The method in claim 1 wherein the condition to be tested is a variance
in supply voltage.

Claim 5 (original): The method in claim 1 wherein the condition to be tested is a variance
in temperature.

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Claim 6 (previously presented): The method of claim 1 wherein the testing step further
comprises:
detecting information concerning defects in the memory; and
counting the number of defects in the memory under each of the plurality of
15 operating environments.

Claim 7 (previously presented): The method in claim 6 wherein the recording step further
comprises:
storing the number of defects detected in the memory.

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Claim 8 (currently amended): The method in claim 7 wherein the comparing step further
comprises:
accessing the stored number of defects to determine if the numbers of defects
detected in the memory under each of the plurality of operating
25 environments are equal to one another;
wherein if the numbers of defects detected in the memory under each of the
plurality of operating environments are equal to one another then the
memory [[can be]] is determined to have integrity.

Claim 9 (previously presented): The method in claim 6 wherein the recording step further comprises:

5 recording and storing the position of each defect detected in the memory under each of the plurality of operating environments.

Claim 10 (previously presented): The method in claim 9 wherein the comparing step further comprises:

10 determining if the positions of defects of the memory under each of the plurality of operating are the same as one another.

Claim 11 (currently amended): A method for determining the integrity of a possibly defected memory, comprising:

15 testing the memory under a first operating environment corresponding to a condition to be tested;

recording a first result of the testing step under the first operating environment;

testing the memory under a second operating environment, wherein the second operating environment corresponds to a variation of the condition to be tested in the first operating environment;

20 recording a second result of the testing step under the second operating environment; and

comparing the first result with the second result, wherein if the first result is equal to the second result then the memory is determined to have integrity.

25 Claim 12 (previously presented): The method of claim 11 wherein the testing steps further comprise:

performing a built-in self test (BIST) on the memory.

Claim 13 (original): The method of claim 12 further comprising:

5 marking a status record memory according to the BIST, wherein the status
record memory corresponds to the memory; and
recording the content of the status record memory for the current operating
environment.

Claim 14 (previously presented): The method in claim 11 wherein the condition to be
tested in the first and the second operating environment is supply voltage.

10 Claim 15 (previously presented): The method in claim 11 wherein the condition to be
tested in the first and the second operating environment is temperature.

Claim 16 (new): The method in claim 11 further comprising:

15 determining whether the first and second results are consistent or inconsistent
with one another.

Claim 17 (new): The method in claim 11 wherein the first result comprises information of
defect locations in the memory corresponding to the first operating
environment and the second result comprises information of defect locations in
20 the memory corresponding to the second operating environment.

Claim 18 (new): A method for determining integrity of a memory with sections that are
possibly defective, the method comprising:

25 repeatedly testing the memory under a plurality of operating environments
respectively corresponding to a given condition to be tested;
recording a result of the testing step for each of the plurality of operating
environments;
comparing the results; and

determining whether the results are consistent or inconsistent with one another;
wherein the results correspond to the given condition, and if they are consistent
with one another the memory is determined to have integrity.

- 5 Claim 19 (new): The method in claim 18 wherein the first result comprises information
 regarding the number of defective sections in the memory corresponding to the
 first operating environment and the second result comprises information
 regarding the number of defective sections in the memory corresponding to the
 second operating environment.

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- Claim 20 (new): The method in claim 18 wherein the first result comprises information
 regarding locations of defective sections in the memory corresponding to the
 first operating environment and the second result comprises information
 regarding locations of defective sections in the memory corresponding to the
15 second operating environment.

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